

IN THE CLAIMS

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1. (Original) A synchronous DRAM comprising:
one memory array divided into a plurality of memory blocks;
mode storage units so disposed in a plurality of stages as to correspond to
said memory blocks, for storing control information for defining operation modes of said
memory blocks;
a setting unit for setting the control information designated by a mode setting
instruction to said mode storage unit corresponding to said memory block designated by
said mode setting instruction in accordance with said mode setting instruction outputted
from a plurality of controllers;
a mode selection unit for selecting said mode storage unit corresponding to
said memory block containing a memory cell designated by an address inputted; and
an access unit for executing an access operation in synchronism with a
predetermined clock signal for the corresponding one of said memory blocks in accordance
with the control information stored in said mode storage unit selected.
2. (Previously Amended) A synchronous DRAM according to claim 1, wherein
said plurality of memory blocks is constituted by continuous memory cells designated by
addresses.
3. (Original) A synchronous DRAM according to claim 1, wherein said plurality
of memory blocks coincides with memory banks.
4. (Original) A synchronous DRAM according to claim 1, wherein said setting
unit includes an object selection unit for selecting said mode storage unit corresponding to
a bit train on the basis of said bit train in the data outputted as a part of said mode setting
instruction from a plurality of controllers, and setting it as a setting object of the control
information.
5. (Original) A synchronous DRAM according to claim 4, wherein said bit train is
a bit train contained in the address outputted to an address bus.

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6. (Original) A synchronous DRAM according to claim 5, wherein said bit train contained in said address is a bit train assigned to a test mode.

7. (Original) A synchronous DRAM according to claim 5, wherein said bit train contained in said address is a bit train assigned to a burst length.

8. (Original) A synchronous DRAM according to claim 5, wherein said bit train contained in said address is a bit train assigned to CAS latency.

9. (Original) A synchronous DRAM according to claim 4, wherein said bit train is a bit train contained in the data outputted to said data bus.

10. (Original) A synchronous DRAM according to claim 4, wherein said setting unit includes an input unit for inputting the control information to said mode storage unit as a setting object on the basis of the bit train outputted as a part of the mode setting instruction by said plurality of controllers to said address bus.

11. (Original) A synchronous DRAM according to claim 1, wherein said mode selection unit includes:

 a selector for acquiring information designating said memory blocks and selecting the control data outputted from the corresponding one of said mode register sets; and

 an address generation unit for generating a series of addresses in accordance with the operation mode inputted.

12. (Original) A synchronous DRAM according to claim 1, wherein said access unit includes:

 an address decoder for decoding an address input and designating the memory cell; and

 an input/output control circuit for executing an access processing

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and

corresponding to the operation mode designated, for the designated memory cell.